



 **MITEL**
SEMICONDUCTOR

SEMICONDUCTOR PRODUCT PROFILE

The high reliability and performance standards along with technology and design capabilities are key ingredients towards a leadership position in any area of the semiconductor industry. It has taken well over a year for Mitel Semiconductor to shed its position as just another good supplier of CMOS integrated circuits by developing a multiplicity of technologies and proprietary designed LSI circuits.

Our capabilities cover a broad spectrum of technologies:

CMOS	Metal Gate & Silicon Gate
PMOS & NMOS	Metal Gate & Silicon Gate
ISO-CMOS	Silicon-Gate
ISO-CCD	Double-Poly

Mitel's proprietary products are grouped into their major functions or applications. These include:

TELECOMMUNICATION CIRCUITS	CMOS/ISO CMOS
TRANSVERSAL FILTERS	ISO-CCD
MEMORIES — CMOS STATIC RAM's/MICROPROCESSORS	ISO CMOS
ALPHA-NUMERIC DISPLAY DRIVERS/DECODERS	CMOS
ANALOG SWITCHES/GATES	CMOS
DETECTORS/TIMERS/ALARMS	CMOS

All products manufactured by Mitel undergo quality inspections and testing in accordance with MIL-M-38510 and MIL-STD-883, Method 5005.1. Reliability screening is in accordance to MIL-STD-883, Method 5004.1, unless specified otherwise in your purchase order.

PRODUCT ASSURANCE

Mitel product undergo the following standard processing, tests and screens:

- WAFER PROBE TEST** — Every die (chip) on the wafer is 100% tested for: Electrical functionality operation. Parametric, AC & DC operation. Parametric leakage (IDD).
- ASSEMBLY** — The assembly of Mitel product is processed to the exacting quality inspection and monitoring standards as specified under MIL-STD-883.
- QUALITY CONTROL** — Visual inspection; all product undergo 100% visual inspection per MIL-STD-883, Method 2010.2, Condition B.
- STABILIZATION BAKE** — Method 1008, C; 150°C, 24 Hours. This heat stresses the device to accelerate degradation failure candidates due to oxide or other process contaminants, and helps to eliminate marginal bonds and electrical connections.
- TEMP. CYCLE** — Method 1010C; -65°C to 150°C, 10 cycles for ceramic packages and 5 cycles for plastic packages. Exposing the product to a 215°C temperature change stresses the chip, wire bonds and package. The extreme temperature variation repeated many times places all parts of the product into a continuous stress mode, and helps accelerate catastrophic failure candidates.
- QUALITY ASSURANCE** — All product, prior to shipment, undergo the following QA Acceptance tests: Functional: 25°C, AQL; 0.28% Plastic — 25°C, AQL; 0.2% Ceramic / DC: 25°C, AQL 0.65% / DC: Temp's AQL 2.2% / AC: 25°C, AQL 1.0%.

In addition to the above standard processes, the following optional screens offer added levels of assurance and reliability to the product:

- FINE LEAK** — Method 1014, B (Tracer-Flo) checks the hermeticity of the ceramic package between 1×10^{-5} and 1×10^{-8} atmcc/sec. leak rates.
- GROSS LEAK** — Method 1014, C checks the package hermeticity up to 1×10^{-5} atmcc/sec.
- BURN-IN** — Method 1015, 125°C for 168 Hours or 150°C for 48 Hours (accelerated).

Continual quality and reliability evaluations are conducted on Mitel products, both in-house and by independent test laboratories. All products undergo periodic quality conformance inspection and testing in accordance with MIL-STD-883, Method 5005.1. Plastic packaged devices undergo added temperature cycling and temperature-humidity (85/85) tests designed to assure the package and product integrity.



DESCRIPTION

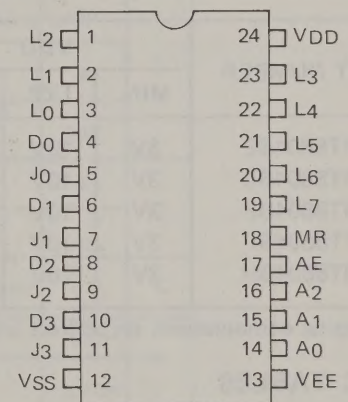
The 8804B is a CMOS/LSI 8 x 4 Analog Switch Array incorporating control memory (32-bits), decoder and digital logic-level convertors. This circuit has digitally controlled analog switches having very low "ON" impedance and very low "OFF" leakage current. Switches will operate with analog signals at frequencies to 40 MHz and up to 18V p-p. A "HIGH" on the Master Reset input switches all channels "OFF" and clears the memory. This device is ideal for crosspoint switching applications. See page 2 for Part Numbers.

- CMOS POWER CONSUMPTION (1 μ W typ.)
- WIDE RANGE OF DIGITAL AND ANALOG SIGNAL LEVELS:
To 18V, ± 9 V peak
- LOW "ON" RESISTANCE: 50 Ω (TYP.)
- MATCHED SWITCH CHARACTERISTICS: 5 Ω (TYP.) BETWEEN RON VALUES
- HIGH "ON/OFF" OUTPUT VOLTAGE RATIO: 65 dB (TYP.) at $f_{is} = 10$ KHz, $R_L = 10$ K Ω
- HIGH DEGREE OF LINEARITY: <0.5% DISTORTION AT $f_{is} = 1$ KHz, $V_{is} = 5$ Vp-p, $V_{DD} - V_{SS} \geq 10$ V, $R_L = 10$ K Ω
- LOW CROSSTALK BETWEEN SWITCHES: -50dB at $f_{is} = 0.9$ MHz, $R_L = 1$ K Ω
- TRANSMITS FREQUENCIES UP TO 40 MHz
- ASYNCHRONOUS MEMORY OPERATION:
- ADDRESS DECODING ON CHIP
- MASTER RESET OF CONTROL MEMORY
- STD. 24-PIN PACKAGES

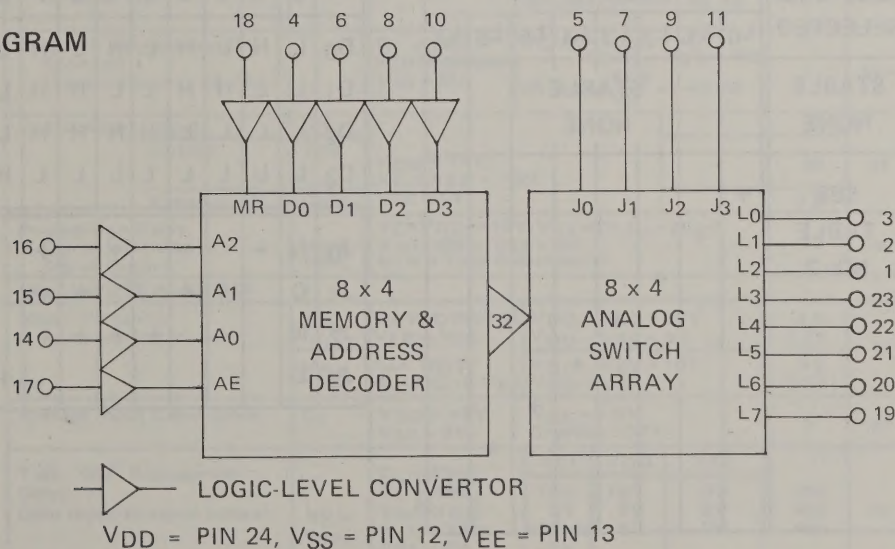
PIN NAMES

A ₀ , A ₁ , A ₂	Address (Active HIGH) Inputs
AE	Address Enable (Active HIGH) Input
MR	Memory Reset (Active HIGH) Input
D ₀ , D ₁ , D ₂ , D ₃	Data (Active HIGH) Inputs
J ₀ , J ₁ , J ₂ , J ₃	Junction (Analog Swx) Inputs
L ₀ , L ₁ , L ₂ , L ₃ , L ₄ , L ₅ , L ₆ , L ₇	Line (Analog Swx) Outputs

CONNECTION DIAGRAM (TOP VIEW)



BLOCK DIAGRAM



FUNCTIONAL DESCRIPTION

The 8804B is a CMOS/LSI 8 x 4 Analog Switch Array designed so that the analog switches can be connected such that the four input junctors may be connected to any combination of the eight output lines depending on what code is stored in the 32-bit memory.

The memory is organized in eight 4-bit words. The logic level signals applied to the four data inputs are transferred to the selected memory locations by the code on the three address inputs whenever a logic HIGH is applied to the address enable input (AE). A logic HIGH set in memory location will cause the corresponding analog switch location to be "ON". A HIGH on the memory reset input (MR) will cause all locations to be in a LOW state and all analog switches to be "OFF".

ABSOLUTE MAXIMUM RATINGS

Voltage at any pin	$V_{SS} - 0.3V$ to $18.5V$
Storage temperature	$-65^{\circ}C$ to $150^{\circ}C$
Operating temperature	$-40^{\circ}C$ to $85^{\circ}C$ and $-55^{\circ}C$ to $125^{\circ}C$

$$V_{DD} - V_{EE} = 18.5V, V_{DD} - V_{SS} = 18.5V$$

GUARANTEED OPERATING RANGES

PART NUMBER	VDD			VEE*			TEMPERATURE	PACKAGE
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.		
MT8804BE	3V	10V	18V	0V	-5V	-15V	$-40^{\circ}C$ to $85^{\circ}C$	24 Pin Epoxy DIP
MT8804BC	3V	10V	18V	0V	-5V	-15V	$-40^{\circ}C$ to $85^{\circ}C$	24 Pin Ceramic DIP
MT8804BF	3V	10V	18V	0V	-5V	-15V	$-55^{\circ}C$ to $125^{\circ}C$	24 Pin Ceramic DIP
MT8804BI	3V	10V	18V	0V	-5V	-15V	$-55^{\circ}C$ to $125^{\circ}C$	24 Pad Tested Chip
MT8804BH	3V	10V	18V	0V	-5V	-15V	$-40^{\circ}C$ to $85^{\circ}C$	24 Pad Tested Chip

* All digital combinations on address and data inputs; all analog inputs: $V_{EE} \leq V_I \leq V_{DD}$

LOGIC TABLES

TABLE NO. 1 – ANALOG SWX. SELECTED

INPUTS						OUTPUTS							
ADDRESS				MEM. RESET	JUNCTOR(S) SELECTED	LINE SELECTED							
A ₀	A ₁	A ₂	A _E			L ₀	L ₁	L ₂	L ₃	L ₄	L ₅	L ₆	L ₇
X	X	X	L	L	STABLE								
X	X	X	X	H	NONE								
L	L	L	H	L	SEE TABLE NO. 2	+							
H	L	L	H	L			+						
L	H	L	H	L				+					
H	H	L	H	L					+				
L	L	H	H	L						+			
H	L	H	H	L							+		
L	H	H	H	L								+	
H	H	H	H	L									+

TABLE NO. 2 – JUNCTOR(S) SELECTED

DATA INPUT CODE																
	0	1	2	3	4	5	6	7	8	9	10	11	12	13	14	15
D ₀	L	H	L	H	L	H	L	H	L	H	L	H	L	H	L	H
D ₁	L	L	H	H	L	L	H	H	L	L	H	H	L	L	H	H
D ₂	L	L	L	L	H	H	H	H	L	L	L	L	H	H	H	H
D ₃	L	L	L	L	L	L	L	L	H	H	H	H	H	H	H	H
J ₀	N	+		+		+		+		+		+		+		+
J ₁	O		+	+			+	+			+	+			+	+
J ₂	N				+	+	+	+					+	+	+	+
J ₃	E								+	+	+	+	+	+	+	+

WHERE:

X = Don't care condition
+ = Selected switch(es)

L = LOW logic state
H = HIGH logic state

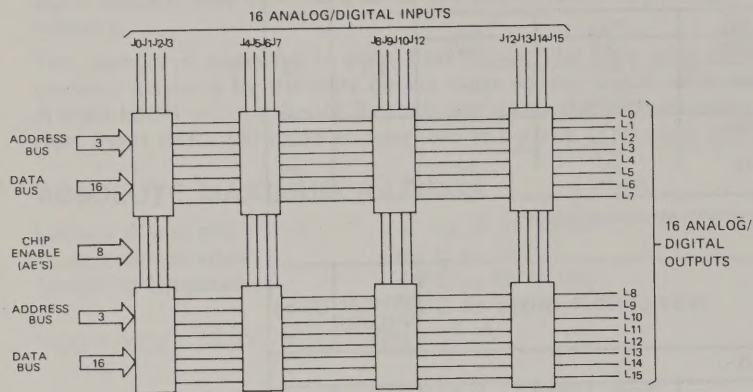
ELECTRICAL CHARACTERISTICS at $T_A = 25^\circ\text{C}$

CHARACTERISTIC	SYMBOL	TEST CONDITIONS			TYPICAL VALUES	UNITS	
Quiescent Device Current	I _L	V _{DD}	V _{SS}	V _{EE}	0.1	μA	
		+10V	0V	0V			
		+5V	0V	-5V			
		NOTE 1					
Quiescent Device Dissipation per Package	P _D	+10V	0V	0V	1	μW	
		+5V	0V	-5V			
		NOTE 1					
NOTE 1: All digital combinations on address inputs; all analog inputs V _{EE} ≤ V _I ≤ V _{DD}							
CHARACTERISTIC	SYMBOL	TEST CONDITIONS			TYPICAL VALUES	UNITS	
SIGNAL INPUTS (V _{is}) AND OUTPUTS (V _{os})							
"ON" Resistance (Peak for V _{SS} ≤ V _{is} ≤ V _{DD})	R _{ON}	R _L = 10kΩ V _{SS} = 0	V _{DD}	V _{EE}	V _{is}	50	Ω
			+9V	-9V	—		
			+18V	0V	—		
			+5V	-5V	—		
Δ "ON" Resistance Between Any 2 Channels	ΔR _{ON}	(Any channel selected)	+10V	0V	—	90	Ω
			+2.5V	-2.5V	—		
			+5V	0V	—		
			+9V	-9V	—		
Sine Wave Response (Distortion)	R _L = 10kΩ V _{SS} = 0 f _{is} = 1kHz	+18V	0V	—	5	Ω	
		+5V	-5V	—			
		+10V	0V	—			
		+2.5V	-2.5V	—			
OFF Channel Leakage Current: Any Channel "OFF" All Channels "OFF"	V _{SS} = 0V	+5V	(= V _C) -5V	—	±0.01	nA	
		+5V	(= V _C) -5V	—	±0.04		
Frequency Response— Channel "ON" (Sine Wave Input)	R _L = 1kΩ V _{is} = 5V (p-p) V _{SS} = 0V	V _C = V _{DD} = +5V, V _{EE} = -5V 20 Log ₁₀ $\frac{V_{OS}}{V_{is}}$ = -3 dB			40	MHz	
Feedthrough Channel "OFF"		V _{DD} = +5V, V _C = V _{EE} = -5V 20 Log ₁₀ $\frac{V_{DS}}{V_{is}}$ = -40 dB			1	MHz	
Crosstalk Between any 2 Channels (Frequency at -40 dB)	R _L = 1kΩ V _{is} (A) = 5V (p-p) V _{SS} = 0V	V _C (A) = V _{DD} = +5V V _C (D) = V _{EE} = -5V 20 Log ₁₀ $\frac{V_{OS}}{V_{is}}$ = -40 dB			1	MHz	
Capacitance: Input	C _{IS}				5	pF	
Output	C _{OS}	V _{DD} = +5V V _C = V _{EE} = -5V V _{SS} = 0V			20		
Feedthrough	C _{IOS}				0.2		
Propagation Delay Signal Input-to- Signal Output	t _{PLH} t _{PHL}	V _C = V _{DD} = +10V, V _{EE} = 0V, C _L = 50 pF V _{is} = 10V*, V _{SS} = 0V t _r , t _f = 20ns (input signal)			10	ns	
(V _C) INPUTS A _i AND D _j							
Noise Immunity (Any control input)	V _{NL}	V _{is} = V _{DD} thru 1kΩ V _{EE} = V _{SS}	V _{DD} - V _{SS} = 10V V _{DD} - V _{SS} = 5V		4.5 2.25	V	
	V _{NH}	I _{is} = 10μA R _L = 1kΩ to V _{EE}	V _{DD} - V _{SS} = 10V V _{DD} - V _{SS} = 5V		4.5 2.25		
Average Input Capacitance	C _I	V _{DD} = +5V V _{SS} = 0V	V _{EE} = -5V Channel "OFF"		5	pF	
Turn "ON" Propagation Delay: ♦ Data Input-to-signal output	t _{PLH} t _{PHL}	C _L = 50pF R _L = 10kΩ V _{is} ≤ V _{DD} t _r , t _f = 20ns V _{SS} = 0V	V _C *	V _{DD}	V _{EE}	200 400 400	ns
			10V	10V	0V		
			5V	5V	0V		
			+5V to -5V	5V	-5V		
Address Enable to-Signal Output		C _L = 50pF R _L = 10kΩ V _{is} = V _{DD} t _r , t _f = 20ns	10V	10V	0V	300	ns
			5V	5V	0V	600	ns
Memory Reset Recovery Time ♦	—	V _{DD} = 10V			200	ns	

- Time after reset is removed during which channel information is invalid / • Square wave / • Symmetrical about 0 volts.
- Channel Overlap = Turn-on propagation delay, where channel overlap is defined as the duration after control signal change during which two channels may be on together.

APPLICATIONS

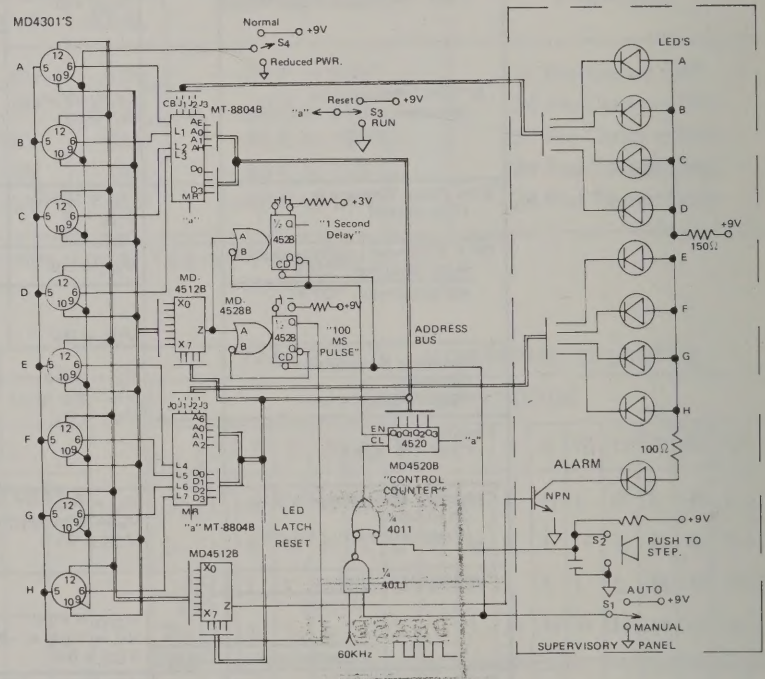
16-INPUT ANALOG MIXER/MULTIPLEXER CIRCUIT



256 switching combinations can be realized using eight MT8804B CMOS/LSI 8 x 4 Analog Switch Arrays. Each of the 16 inputs can be connected to any of the 16 outputs simultaneously. The address input will select the output line, while the data input will select the junctor input or combination of inputs to be switched onto the selected output line.

MULTIPLE-DETECTOR/ALARM SYSTEM WITH REMOTE AUTOMATIC SUPERVISORY DISPLAY AND CONTROL PANEL.

The address control counter (MD4520B) causes the eight detector (MD4301A's) locations to be scanned once every 267 μ S. If any detector is activated in any way, the counter will immediately stop at that location. The situation can be quickly analysed using the supervisory panel as follows:



PANEL INDICATION*			INDICATED CONDITION
HORN	ALARM LIGHT	LED'S	
No Sound	OFF	Pulsing	Normal — Standby
ON	ON	ON	Continuously Activated Detector (s).
Pulsed	Pulsed	Pulsing	Momentarily Activated Detector (s).
Pulsing	OFF	Pulsing	Low Battery Voltage at Location (s).

*S₁ = Auto; S₂ = OFF; S₃ = RUN; S₄ = Don't Care

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**MITEL**

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MITEL SEMICONDUCTOR PRICE GUIDE

PART NUMBER	DESCRIPTION	1-24	24-99	100	1000	10,000
MH88200	DTMF RECEIVER	98.00	98.00	90.00	79.00	75.00
MT8820AN	DTMF DECODER	37.50	31.25	25.00	17.60	15.00
MT8820AJ		41.25	34.40	27.50	19.40	16.50
MT8804BN	8 X 4 M U X	10.75	8.95	7.15	6.30	5.50
MT8804BJ		12.90	10.75	8.60	7.80	7.00
ML8204AE	TONE RINGER	2.40	2.00	1.60	1.36	1.25
ML8204AE-1		2.25	1.89	1.50	1.35	1.15
MD4301/03AC	TIMER	3.15	2.65	2.10	1.80	1.50
MD4302/04AE		2.25	1.89	1.50	1.30	1.10
MD4302/04AE-1		2.25	1.89	1.50	1.35	1.15
MD4330/31BS	LCD DRIVER	4.20	3.50	2.80	2.55	2.30
MD4330/31BM		8.25	6.90	5.50	5.00	4.50
MD4332BS		4.35	3.65	2.90	2.65	2.40
MD4311/4511BE	DISPLAY DRIVER	2.10	1.75	1.40	.80	.70
MD4368BE		2.20	1.82	1.45	.85	.75
MD4368BC		2.95	2.45	1.95	1.15	.95
SIL1902AE	1K RAM	15.00	12.50	10.00	7.80	5.50
SIL1902AC		16.20	13.50	10.80	8.40	5.90
MD4508BN	DECODER LATCH	3.70	3.07	2.45	1.25	1.15
MD4514/15BN		3.70	3.07	2.45	1.25	1.15
MD4528BE		1.50	1.25	1.00	.60	.58
MD4046BE	PHASE LOCK LP	2.10	1.75	1.40	.80	.70
MD4046BC		2.80	2.35	1.85	1.10	.90

The package, temperature range and supply voltage range for each follows:

PREFIX	SUFFIX
MA/ML - Linear	A.- Non-standard
MD - Digital	Parameters
MT - Telecom	B.- Generally, Std.
MH - Hybrid	JEDEC-B Spec.
SIL - Siltek	Parameters (3-18V)

E.G. PREFIX DEVICE SUFFIX
MT 8804 BJ/B
3V-18V operation ——— ↑ ↑ ↑
Package, Temperature ——— ↑
*MIL Process Option ——— ↑
*MIL-STD-883, 5004.1, 125°C/168 Hr
or 150°C/48 Hrs. Burn-in.

PACKAGE STYLE, TEMPERATURE RANGE

C-Ceramic DIP, 8-18 pins, -40°C to 85°C	M-Ceramic DIP, 40 pins, -40°C to 85°C
E-Plastic DIP, 8-18 pins, -40°C to 85°C	N-Plastic DIP, 24 pins, -40°C to 85°C
J-Ceramic DIP, 24 pins, -40°C to 85°C	S-Plastic DIP, 40 pins, -40°C to 85°C

MINIMUM ACCEPTABLE ORDER IS \$100.

DETECTORS – TIMERS – ALARMS:

CMOS/ LSI Detector/Timer	
Without protected MOSFET Input –	MD4301A
With protected MOSFET Input –	MD4301B

DISPLAY DRIVERS – DECODERS:

CMOS/MSI 7-Segment Hexadecimal	MD4368A
Decoder/Driver/Latch	MD4368B
7-Segment Hexadecimal	MD4311A
Decoder/Driver/Latch	MD4311B
7-Segment BCD Decoder/	MD4511A
Driver/Latch	MD4511B
CMOS/ LSI 30-Bit LCD Driver/Register	MD4330B
CMOS/MSI 7-Segment LCD Decoder/Driver	MD4055B
CMOS/MSI 7-Segment LCD Decoder/Driver Latch	MD4056B

SHIFT REGISTERS – COUNTERS:

CMOS/MSI 4-Bit Parallel In/Out	SIL4035B
CMOS/MSI Dual 4-Bit Serial In/Parallel Out	SIL4015B
CMOS/MSI 8-Bit Sync. Parallel In/Serial Out	SIL4014B
CMOS/MSI 8-Bit Assync. Parallel In/Serial Out	SIL4021B
CMOS/MSI 12-Stage Binary Counter	SIL4040B
CMOS/MSI 14-Stage Binary Counter	SIL4020B
CMOS/MSI 14-Stage Binary Counter with Osc.	SIL4060B
CMOS/MSI Dual BCD Counter (sync.)	SIL4518B
CMOS/MSI Dual Binary Counter (sync.)	SIL4520B
CMOS/MSI Decode Counter/Divider	SIL4017B
CMOS/MSI Divide-by-8 Counter/Divider	SIL4022B
CMOS/MSI Presettable Divide-by-N Counter	SIL4018B
CMOS/MSI Presettable BCD/Binary – UP/DN Counter	SIL4029B
CMOS/MSI Presettable BCD/ UP/DN Counter	SIL4510B
CMOS/MSI Presettable Binary UP/DN Counter	SIL4516B

ANALOG SWITCHES – MULTIPLEXERS:

CMOS/ LSI 8 x 4 Analog Switch Array With Memory	MT8804A
CMOS/ LSI 8 x 4 Analog Switch Array With Memory	MT8804B
CMOS/MSI Quad Bilateral Analog Switch –	SIL4016B
CMOS/MSI Quad Bilateral Analog Switch –	SIL4066B
CMOS/MSI 8-Channel Analog Multiplexer –	SIL4051B
CMOS/MSI 4-Channel Differential Analog Multiplexer	SIL4052B
CMOS/MSI Triple 2-Channel Analog Multiplexer –	SIL4053B
CMOS/MSI 8-Channel Data Selector –	SIL4512B

DECODERS – LATCHES:

CMOS/ LSI Dual 4-Bit Latch	MD4508B
CMOS/ LSI 4-Bit Latch/4 to 16 Decoder	MD4514B
CMOS/ LSI 4-Bit Latch/4 to 16 Decoder	MD4515B
CMOS/MSI Quad Clocked "D" Latch –	SIL4042B
CMOS/MSI Quad NOR R/S Latch –	SIL4043B
CMOS/MSI Quad NAND R/S Latch –	SIL4044B
CMOS/MSI Quad 3-State "D" Latch –	SIL4076B

ISO-CMOS TECHNOLOGY

MOS has grown into its present market size by virtue of its economic advantages over other forms (technologies) for circuit design. This cost advantage can ultimately be traced back to the silicon area used to implement a circuit. Since MOS devices are mostly surface devices, the smallest size can be related directly to the number of transistors, the size of each transistor, and the area required to isolate transistors from each other. Silicon-Gate MOS because of its self-aligning gate-source-drain processing characteristic, has become a standard for the MOS/LSI world. Silicon-Gate also provides an additional layer of interconnect using the poly-silicon gate material.

CMOS (complementary MOS) processing found a home in the MOS market by virtue of two unique features not available in single channel (PMOS & NMOS) processing. One being its ability to operate at very low supply voltages (under 3 volts), since the logic levels on chip are the full supply rails. Secondly, CMOS logic dissipates no power in the quiescent state and the only power used is when switching from one state to another. CMOS processing has not made many inroads into the MOS/LSI marketplace to-date mainly because of the silicon area required to isolate one transistor from another was prohibitively large.

Mitel Semiconductor has combined mature processing steps used throughout the industry to make CMOS circuits at the same (or smaller) density as single channel MOS processing. The process topology is shown in Figure 1, and is named "ISO-CMOS". This process offers all the advantages of CMOS at an area per function of PMOS or NMOS processing and is completely self-aligning throughout the process. With the reduction of area another advantage of the process becomes apparent. Switching speed in this process approaches that of TTSL Bipolar processes.

TOPOLOGY - ISO-CMOS

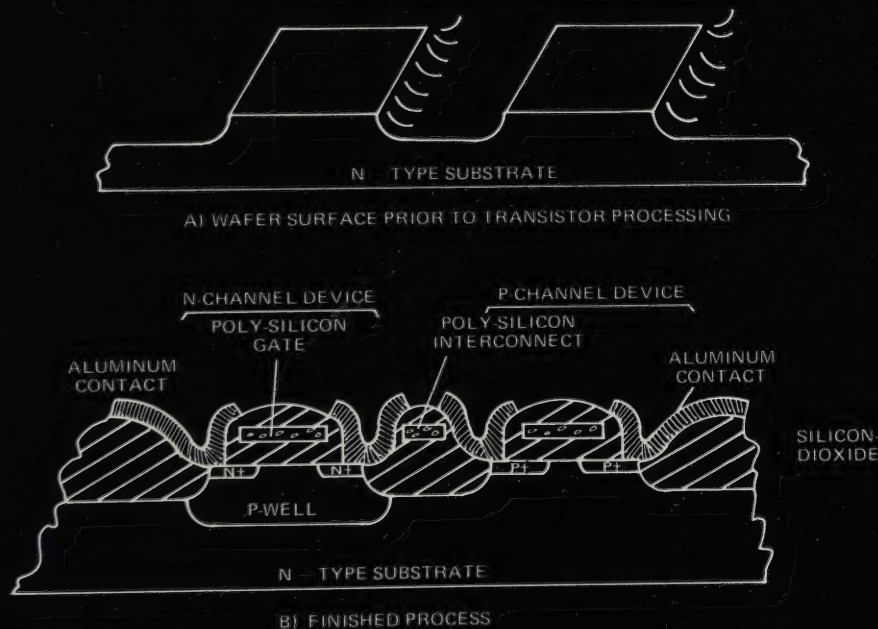
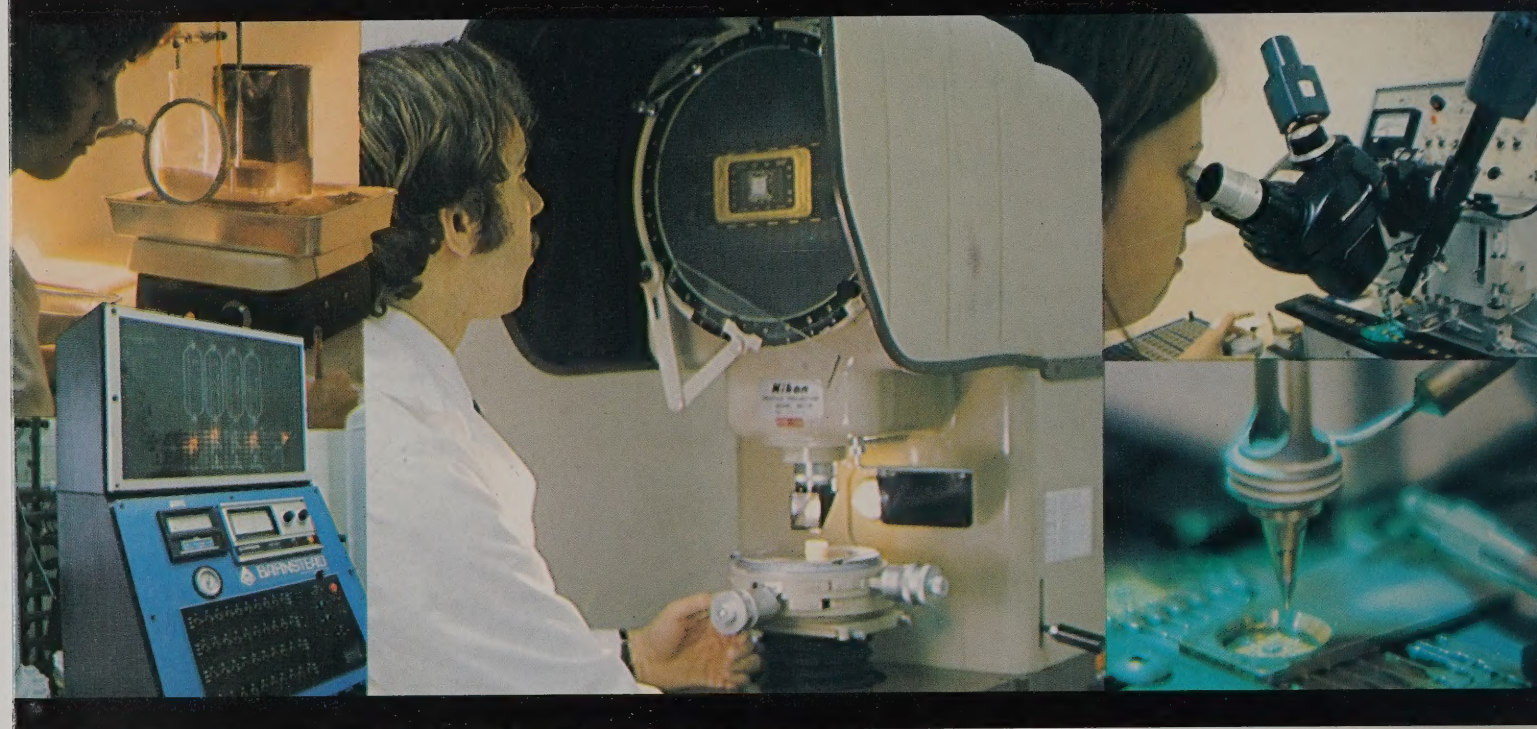


FIGURE 1.



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